

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI ULBM2 is Designed for

**FEATURES:**

- 
- 
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	0.75 A
<b>V<sub>CBO</sub></b>	36 V
<b>V<sub>CEO</sub></b>	16 V
<b>V<sub>CES</sub></b>	36 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	5 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	35 °C/W

**PACKAGE STYLE .280 4L STUD**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**ORDER CODE: ASI10675**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 25 mA	16			<b>V</b>
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 5.0 mA	36			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	4.0			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CE</sub> = 15 V			1.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V    I <sub>C</sub> = 100 mA	20	---	---	---
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 12 V    f = 1.0 MHz			10	<b>pF</b>
<b>P<sub>G</sub></b> <b>η<sub>C</sub></b>	V <sub>CC</sub> = 12.5 V    P <sub>OUT</sub> = 2.0 W    f = 470 MHz	10	60		<b>dB</b> <b>%</b>